

Performance Features:

- Frequency band: 2~4GHz
- Insertion loss: 0.5dB
- Fluctuation of insertion loss: ± 0.2 dB
- Isolation: 20dB
- Input/output return loss: 20dB/20dB
- Chip size: 1.3mm \times 1.1mm \times 0.1mm

Product Description:

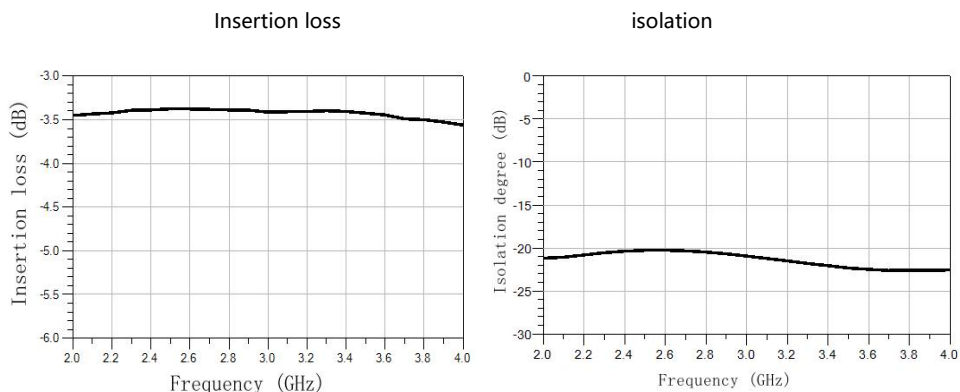
CW-PD0204V is a GaAs MMIC^o two-way power splitter chip. The power splitter chip has the characteristics of small plug loss, high isolation, small size, easy integration and so on. It is widely used in power distribution and synthesis. Its frequency range covers 2~4GHz, and the insertion loss is less than 0.7dB in the whole frequency band.

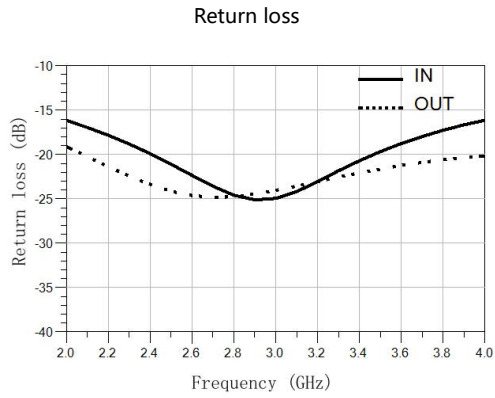
Electrical parameters: ($T_A=25^\circ\text{C}$)

Indicators	Minimum	Typical value	Maximum value	Units
Frequency range	2~4			GHz
Insertion loss	-	0.5	-	dB
Fluctuations in plug loss	-	-	± 0.2	dB
isolation	20	22	-	dB
Input return loss	-	20	-	dB
Output return loss	-	20	-	dB

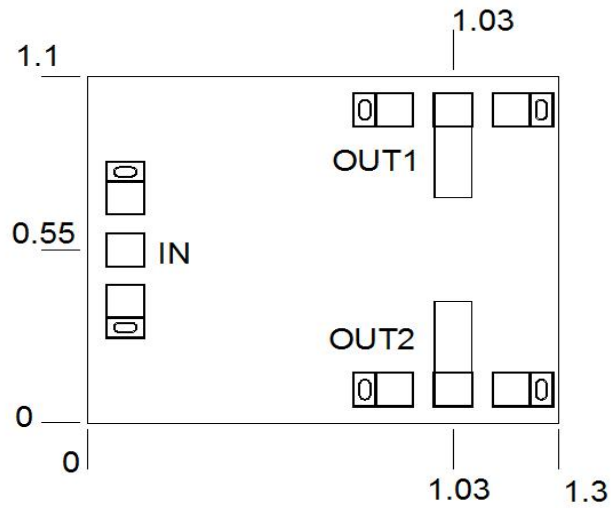
Use limiting parameters:

Input power	+27dBm
Storage temperature	-65 $^\circ\text{C}$ ~150 $^\circ\text{C}$
Service temperature	-55 $^\circ\text{C}$ ~85 $^\circ\text{C}$

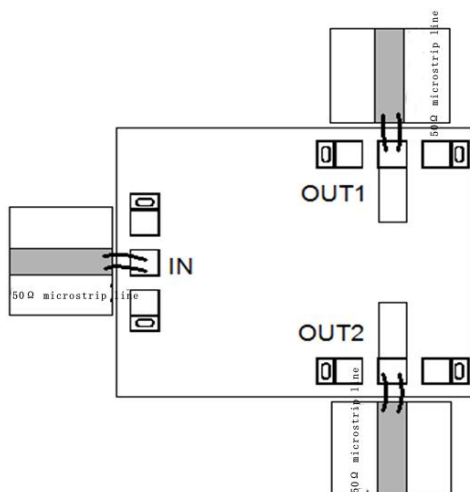
Typical curve:



Size drawing: (unit mm)



Suggested assembly drawing:



Instructions:

Storage: The chip must be placed in a container with electrostatic protection and stored in a nitrogen environment.

Cleaning treatment: The bare chip must be operated and used in a purified environment. It is forbidden to use liquid cleaning agent to clean the chip.

Electrostatic protection: Strictly comply with the ESD protection requirements to avoid electrostatic damage to the components.

General operation: Use vacuum chuck or precision pointed tweezers to pick up the chip. Avoid touching the surface of the chip with tools or fingers during handling.

Mounting operation: The chip can be installed using AuSn solder eutectic welding or conductive adhesive bonding process. The mounting surface must be clean and flat.

Bonding operation: Input and output with 2 (recommended diameter of 25μm gold wire) bonding wire, bonding wire length less than 250μm is optimal. It is recommended to use the smallest possible ultrasonic energy. Bonding begins at the pressure point on the chip and ends at the package (or substrate).